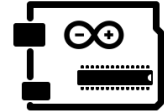
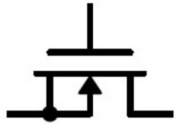




Micron Technology, Inc.



# Large Scale DRAM Array Model



"DRAM ENGINEERS"

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Capstone Mentor: Ashwija Korenda, Teaching Assistant  
Faculty Mentor: Julie Heynssens, NAU Lecturer



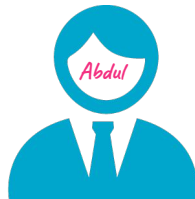


## Our Client

*Daniel Eichenberger*

Test engineer from Micron Technology, INC.

- ❑ Requested an eight by eight DRAM array model.
- ❑ Plans to use the DRAM model as a demonstration of DRAM functions to prospective memory and Micron engineers.



# Introduction

## Goals:

- ✓ *General Purpose*  
Build a DRAM array with external controller (Arduino Mega) and a robust board.
- ✓ *DRAM array*  
Contains 8 by 8 DRAM cells connected with 8 word-lines and 8 digit-lines, which could be controlled manually using push buttons to select a cell and toggle switch to select what to write.

## Goals:

- ✓ *Arduino Mega*  
Allows user to send the certain address of digitlines and wordlines and charges the DRAM array automatically.
- ✓ *Carrying Board*  
Be large enough to hold the DRAM array, Arduino and battery.



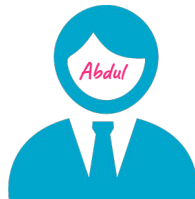
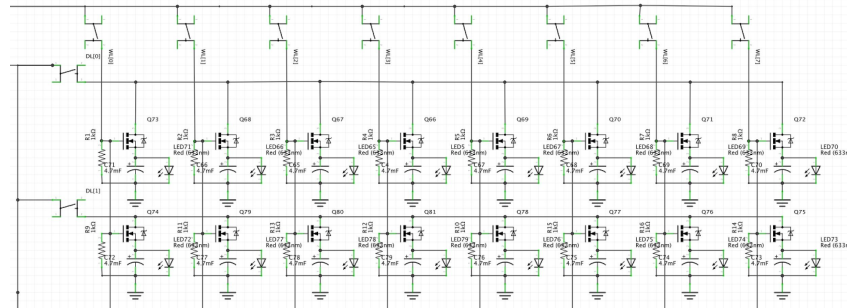
$$\sin\left(\omega t + \frac{\pi}{2}\right)$$



# Project Overview

Our project consists of 3 main subsystems

01. DRAM Array
  - a. The user will be able to write to, read from, and refresh the array using external inputs.
  - b. The array is comprised of sixty-four cells.
  - c. An LED on each cell will show the user if a "1" or "0" by brightening or dimming.

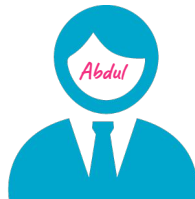
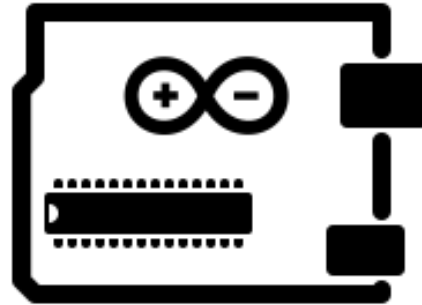


# Project Overview

Our project consists of 3 main subsystems

## 02. Microcontroller

- a. The microcontroller will access specific m-bit cells for the user.
- b. Users use the serial monitor to enter digit and wordline addresses.
- c. LEDs on the array will show which cell was written to for a short period of time.

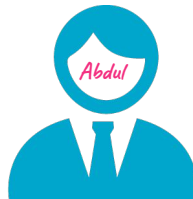
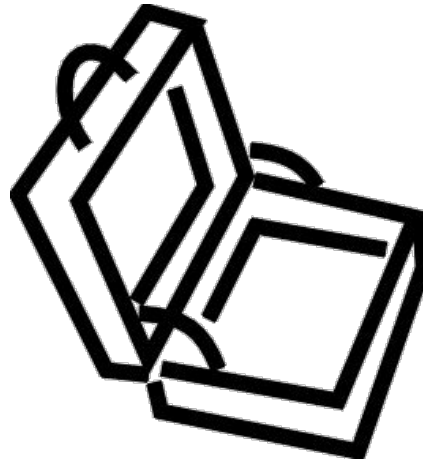


# Project Overview

Our project consists of 3 main subsystems

## 03. Carrying Board

- a. The model will be completely safe and portable on a carrying board.
- b. Overall, the model measures 20" x 7" x 6"(L x W x H).



# Project Process

- ✓ Fall 2017: Theory Analysis and Design Assumptions
  - ✓ Early Spring 2018: Circuit Design and Manual Tests
  - ✓ Later Spring 2018: Software Implementation and Final Tests
- ❑ There were other design ideas we made in the first semester.
  - ❑ After several tests, the results showed the best design solution that satisfied all of our DRAM requirements.



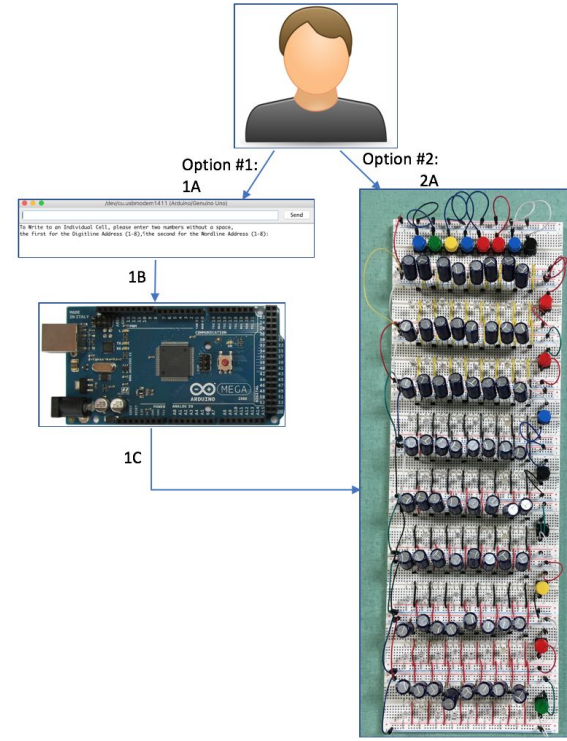
# The DRAM Model process

## Option 1

- A. User is prompted by software to enter WL (wordline) and DL (digitline).
- B. The microcontroller writes to the user's selected array address.
- C. Displays on the DRAM 64 mbit cell array

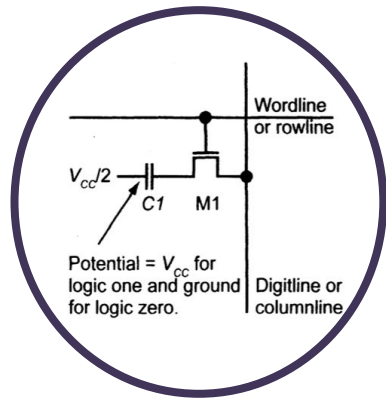
## Option 2

- A. Manually write to the array by interacting with the push buttons on wordlines and digitlines and toggle switch for writing a "1" or "0".

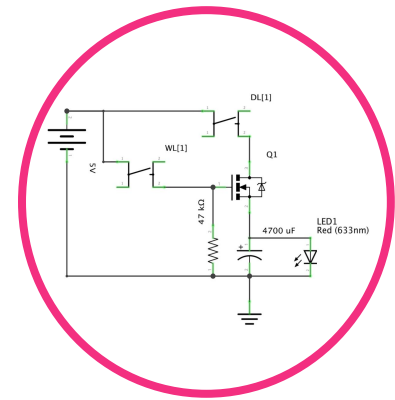




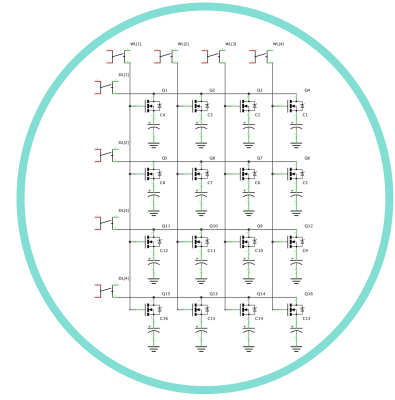
# The details are in the Cell



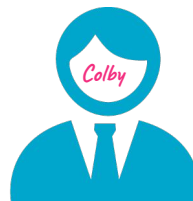
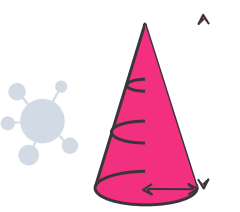
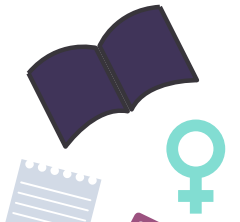
Theoretical m-bit schematic



M-bit schematic used in model



Grid-connected configuration



# Project Challenges

## *Design of the DRAM Array*

Construction in an 8x8 grid-connected configuration:

- ❑ Floating gates on the transistors led to multiple cells being able to be accessed at once.
- ❑ Resistors tied to ground at the gates eliminated this problem.

## *Programming the Microcontroller*

Interfacing with the Array:

- ❑ Arduino voltage not large enough to light every cell.
- ❑ 9V battery implemented to power the entire array.
- ❑ Arduino now used exclusively for optional software access to the array.



# LIVE DEMONSTRATION



# Conclusion

- Daniel Eichenberger requested a functional 8 by 8 DRAM array to emulate DRAM functions.
- Our project consists of the three main subsystems:
  - ◆ Array, Microcontroller, and Carrying board.
- We have met all of the needs and requirements from our client and is satisfied with the model.
- Our client plans to demonstrate this model for future career fairs and prospective memory engineers.



## For more information, refer to the following:

- ❑ “DRAM ENGINEERS” Team Website

<https://www.cefns.nau.edu/capstone/projects/EE/2018/DRAMBoard>

- ❑ Micron Technology Website

<https://www.micron.com>



# Thank you!

Questions?

